



PJS6401

30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

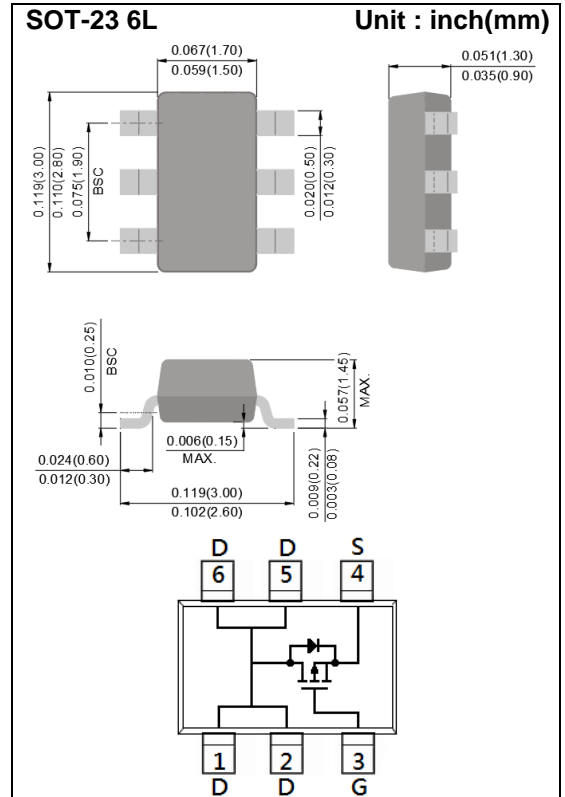
-4.6A

Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-4.6A < 71m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-3.3A < 81m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-2.5V$, $I_D@-1.8A < 110m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: S01



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-4.6	A
Pulsed Drain Current	I_{DM}	-18.4	A
Power Dissipation	P_D	$T_a=25^\circ C$	2
		Derate above $25^\circ C$	16
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ C$
Typical Thermal Resistance	$R_{\theta JA}$	62.5	$^\circ C/W$
- Junction to Ambient ^(Note 3)			



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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.5	-0.96	-1.3	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4.6A	-	60	71	mΩ
		V _{GS} =-4.5V, I _D =-3.3A	-	67	81	
		V _{GS} =-2.5V, I _D =-1.8A	-	84	110	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	±10	±100	nA
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-4.6A, V _{GS} =-10V(Notes 1,2)	-	15.5	-	nC
Gate-Source Charge	Q _{gs}		-	1.5	-	
Gate-Drain Charge	Q _{gd}		-	2.2	-	
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1.0MHZ	-	637	-	pF
Output Capacitance	C _{oss}		-	50	-	
Reverse Transfer Capacitance	C _{rss}		-	35	-	
Switching						
Turn-On Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-4.6A, V _{GS} =-10V, R _G =6Ω(Notes 1,2)	-	3	-	ns
Turn-On Rise Time	t _r		-	43	-	
Turn-Off Delay Time	t _{d(off)}		-	224	-	
Turn-Off Fall Time	t _f		-	101	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	-2.0	A
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0V		-0.75	-1.2	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited



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TYPICAL CHARACTERISTIC CURVES

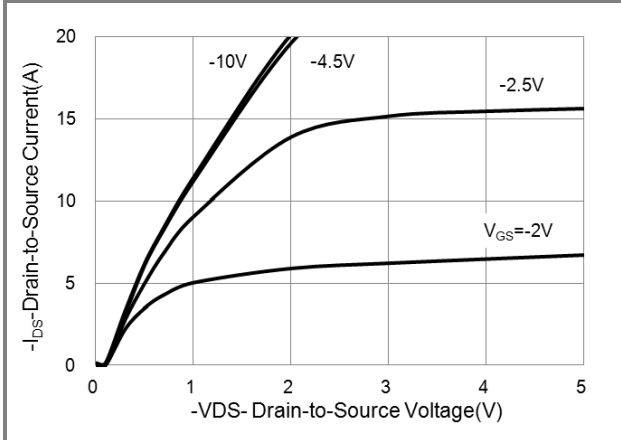


Fig.1 On-Region Characteristics

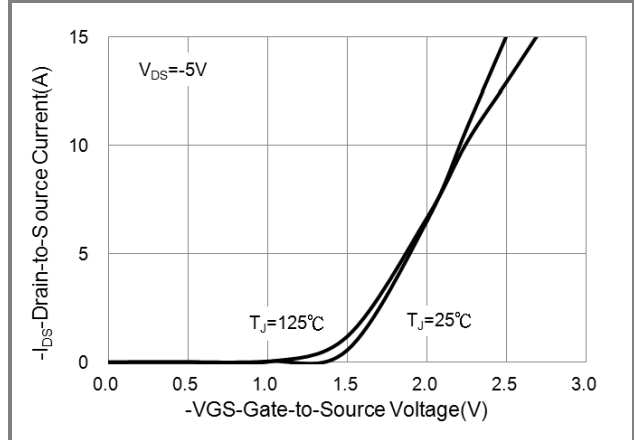


Fig.2 Transfer Characteristics

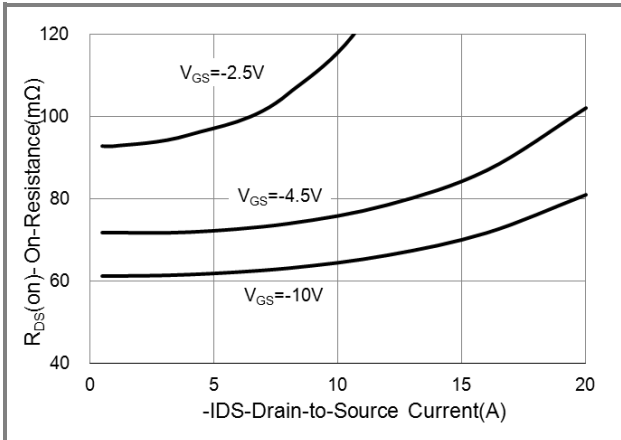


Fig.3 On-Resistance vs. Drain Current

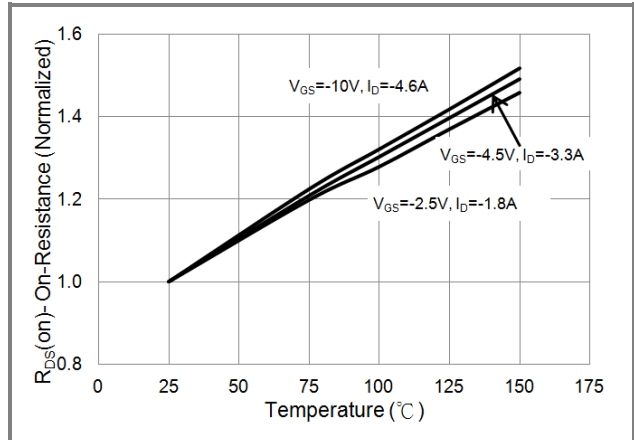


Fig.4 On-Resistance vs. Junction temperature

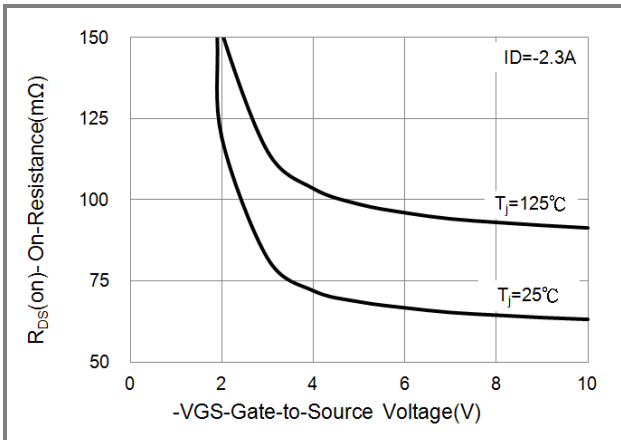


Fig.5 On-Resistance Variation with VGS.

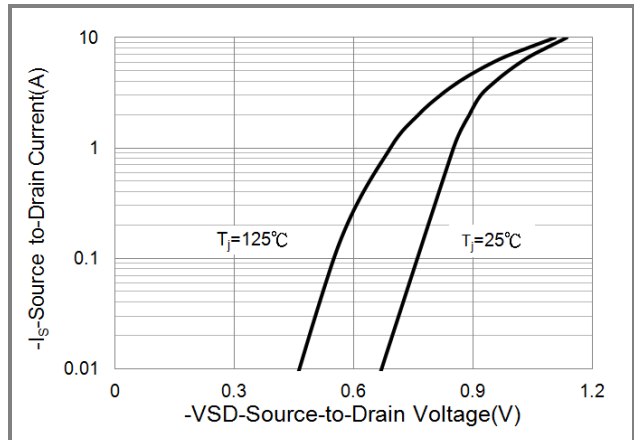


Fig.6 Body Diode Characteristics



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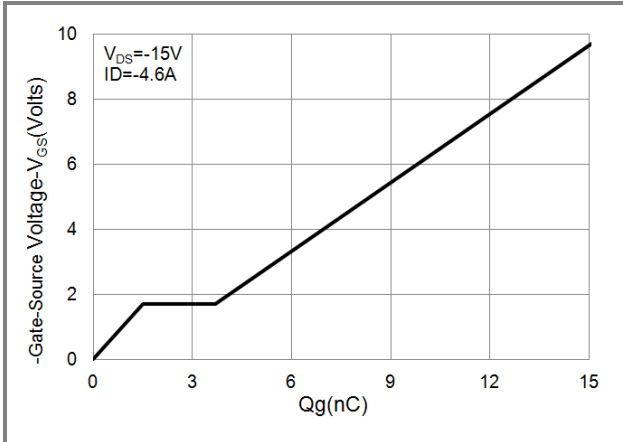


Fig.7 Gate-Charge Characteristics

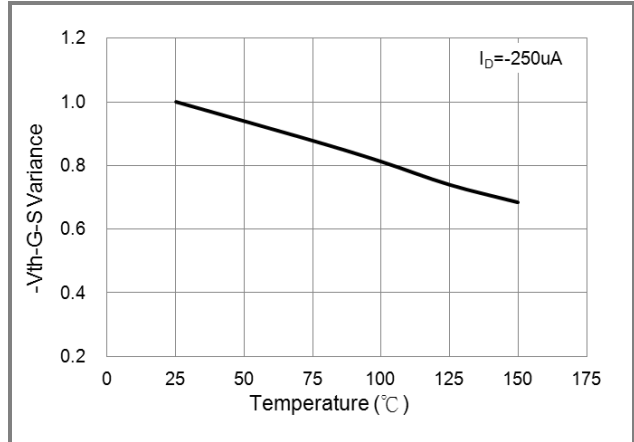


Fig.8 Threshold Voltage Variation with Temperature.

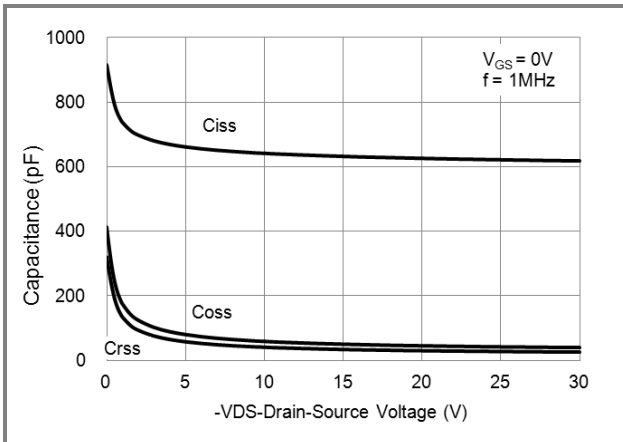


Fig.9 Capacitance vs. Drain-Source Voltage.



PJS6401

PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6401_S1_00001	SOT-23 6L	3K pcs / 7" reel	S01	Halogen free RoHS compliant
PJS6401_S2_00001	SOT-23 6L	10K pcs / 13" reel	S01	Halogen free RoHS compliant

MOUNTING PAD LAYOUT

